



			1100		1100	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	0	80	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	PES	80	$V_0$
Emitter-base voltage (open collector)	$-V_{EBO}$	max.		4	V	
Collector current (d.c.)	$-I_C$	max.		500		mA
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	Ptot			250		mW
D.C. current gain						
$-I_C = 100 \text{ mA}; -V_{CE} = 1 \text{ V}$	$h_{FE}$	min.		100		
Transition frequency at $f = 100 MHz$						
$-I_C = 100 \text{ mA}; -V_{CE} = 1 \text{ V}$	$f_T$	min.		50		MHz
Collector-emitter saturation voltage						
$-I_C = 100 \text{ mA}; I_B = 10 \text{ mA}$	<b>V</b> CEsat	max.		0.25		V



# CMBTA55 CMBTA56

### **RATINGS** (at $T_A = 25^{\circ}C$ unless otherwise specified) Limiting values

		CMBT	A55	A5	6
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	80	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.		4	V
Collector current (d.c.)	$-I_C$	max.		500	mА
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	P <sub>tot</sub>	max.		250	mW
Storage temperature	T <sub>stg</sub>		-55	to +150	° C
Junction temperature	Τj	max.		150	° C

#### THERMAL CHARACTERISTICS

$T_j = P (R_{th j-t} + R_{th t-s} + R_{th s-a}) + T_{amb}$			
Thermal resistance			
from junction to ambient	R <sub>th j-a</sub>	500	K/W

## **CHARACTERISTICS** (at $T_A = 25^{\circ}C$ unless otherwise specified)

Collector-emitter breakdown voltage	CMBTA55				A56	
$-I_C = 1 mA; I_B = 0$	$-V_{(BR)CEC}$	omin.	60		80 V	
Emitter-base breakdown voltage						
$-I_C = 0; I_E = 100 \ \mu A$	$-V_{(BR)EBC}$	) min.		4	V	
Collector cut-off current						
$-V_{CE} = 60 V; I_B = 0$	$-I_{CEO}$	max.		0.1	$\mu A$	
$-V_{CB} = 60 V; I_E = 0$	$-I_{CBO}$	max. (	0.1		- μA	
$-V_{CB} = 80 V; I_E = 0$	-I <sub>CBO</sub>	max.			<i>0.1</i> μ <i>A</i>	
Saturation voltages						
$-I_C = 100 \ mA; \ -I_B = 10 \ mA$	-V <sub>CEsat</sub>	max.		0.25	V	
Base-emitter On voltage						
$-I_C = 100 \text{ mA; } -V_{CE} = 1 \text{ V}$	$-V_{BE(on)}$	max.		1.2	V	
D.C. current gain						
$-I_C = 10 \text{ mA; } -V_{CE} = 1 \text{ V}$	$h_{FE}$	min.		100		
$-I_C = 100 \text{ mA; } -V_{CE} = 1 \text{ V}$	$h_{FE}$	min.		100		
Transition frequency at $f = 100 \text{ MHz}$						
$-I_C = 100 \text{ mA; } -V_{CE} = 1 \text{ V}$	$f_T$	min.		50	MHz	

**Customer Notes** 

## Disclaimer

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